

1. Scope :

This specification applies to silicon zener double diodes chips,
Device NO. SD-61169

2. Structure :

- 2-1. Planar type : NPN, Zener Double Diodes.
- 2-2. Electrodes :
Top side : Aluminum alloy .
Back side : Isolation layer.

3. Size :

- 3-1. Chip size : 10.0 ± 0.6 mils x 10.0 ± 0.6 mils (0.255 ± 0.015 mm x 0.255 ± 0.015 mm).
- 3-2. Chip thickness : 6.0 ± 1.0 mils (0.150 ± 0.025 mm).
- 3-3. Active area : 7.3 mils x 7.3 mils x 1/2 x 2 (0.186 mm x 0.186 mm x 1/2 x 2).
- 3-4. Dual Bonding pad : 6.8 mils x 6.8 mils x 1/2 x 2 (0.173 mm x 0.173 mm x 1/2 x 2) .
Hight of hypotenuse : 5.23 mils (0.133 mm)
- 3-5. Pattern drawing : Refer to the attached drawing

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I _R	V _R =4V E _e =0mW/cm ²			100	nA
		V _R =5V E _e =0mW/cm ²			0.5	μA
Zener Voltage	V _Z	I _Z =5mA E _e =0mW/cm ²	6.4		7.6	V

